



PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q61572

Noriaki ODA

Appln. No.: 09/739,620

Group Art Unit: 2812

Confirmation No.: 4739

Examiner: Ha Nguyen

Filed: December 20, 2000

For: SEMICONDUCTOR DEVICE WITH COPPER-BASED WIRING LINES AND  
METHOD OF FABRICATING THE SAME

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3/7/3  
RECEIVED  
MAR -4 2003  
TECHNOLOGY CENTER 2800

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner for Patents  
Washington, D.C. 20231

Sir:

In response to the Office Action dated December 3, 2002, please amend the above-identified application as follows:

**IN THE CLAIMS:**

**Please enter the following amended claims:**

10. (Amended) The device according to claim 1, wherein the dielectric in which the wiring line is buried has a composite structure comprising a first dielectric layer, an etch stop layer formed on the first dielectric layer, and a second dielectric layer formed on the etch stop layer;